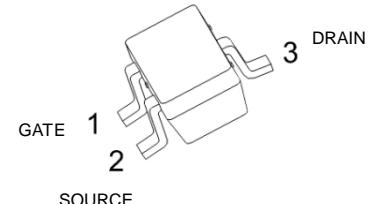
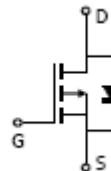




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## MT3407 P-Channel 30-V(D-S) MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}\text{MAX}$	$I_D$
-30V	60m $\Omega$ @-10 V	-4.1A
	87m $\Omega$ @-4.5V	



### General Description

The MT3407 uses advanced trench technology to provide excellent  $R_{DS(on)}$  with low gate charge. This device is suitable for use as a load switch or in PWM applications.

**MARKING : R7**

**SOT23-3L**

### Maximum ratings ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Units
Drain-Source voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	-4.1	A
Drain Current-Pulsed	$I_{DM}$	-20	A
Power Dissipation	$P_D$	300	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{STG}$	-55~+150	°C



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## MOSFET ELECTRICAL CHARACTERISTICS

T<sub>a</sub>=25 °C unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static characteristics</b>						
Drain-source breakdown voltage	V <sub>(BR) DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-30			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V			-1	μA
Gate -source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	nA
Drain-source on-resistance (note 1)	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -4.1A		50	60	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3A		68	87	mΩ
Forward tranconductance (note 1)	g <sub>FS</sub>	V <sub>DS</sub> = -5V, I <sub>D</sub> = -4A	5.5			S
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-1	-1.4	-3	V
Diode forward voltage (note 1)	V <sub>SD</sub>	I <sub>S</sub> = -1A, V <sub>GS</sub> = 0V			-1	V
<b>Dynamic characteristics (note 2)</b>						
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1MHz		700		pF
Output capacitance	C <sub>oss</sub>			120		pF
Reverse transfer capacitance	C <sub>rss</sub>			75		pF
<b>Switching characteristics (note 2)</b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -15V, R <sub>L</sub> = 3.6Ω, R <sub>GEN</sub> = 3Ω		8.6		ns
Turn-on rise time	t <sub>r</sub>			5.0		ns
Turn-off delay time	t <sub>d(off)</sub>			28.2		ns
Turn-off fall time	t <sub>f</sub>			13.5		ns

### Notes:

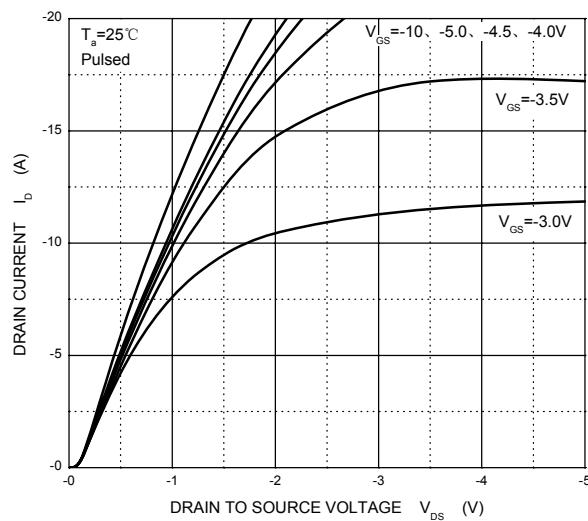
1. Pulse test: Pulse width ≤300μs, Duty cycle ≤2%.
2. These parameter have no way to verify.



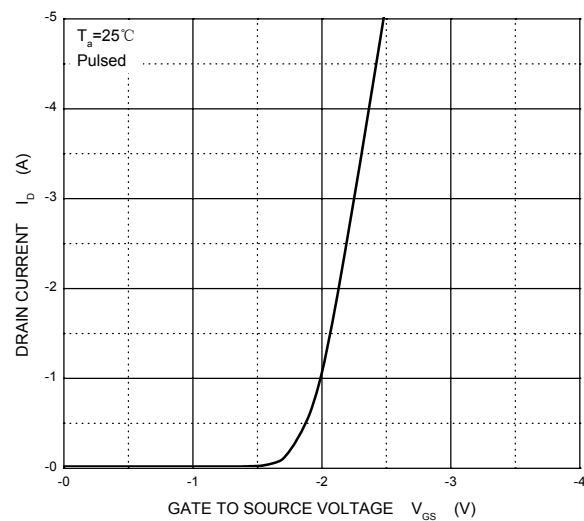
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## Typical Characteristics

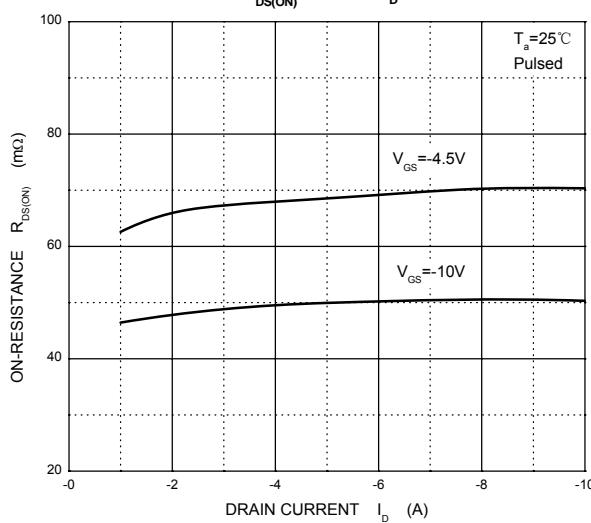
Output Characteristics



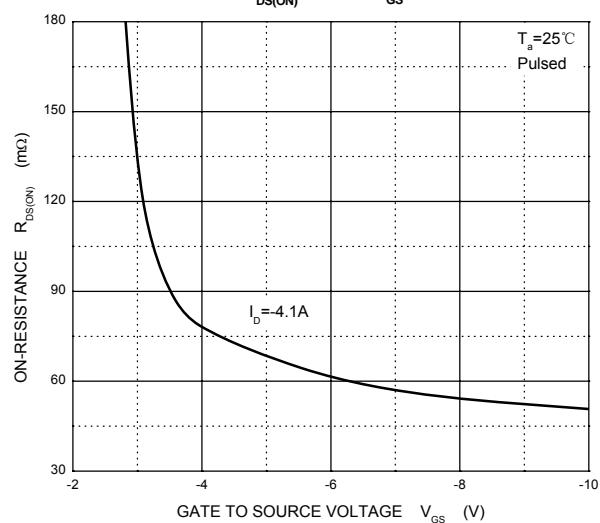
Transfer Characteristics



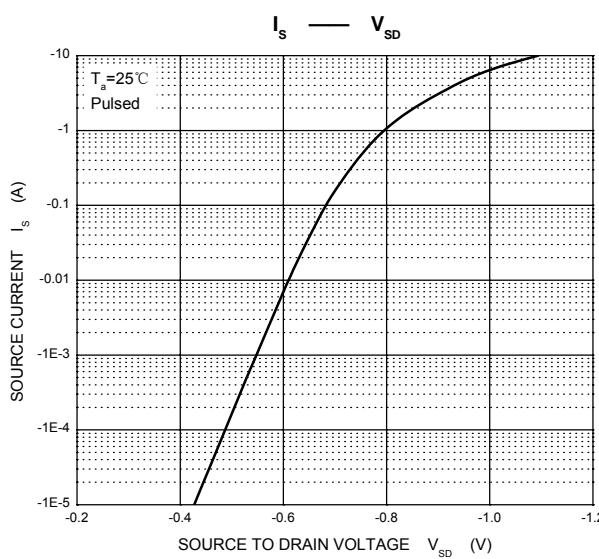
$R_{DS(ON)}$  —  $I_D$



$R_{DS(ON)}$  —  $V_{GS}$



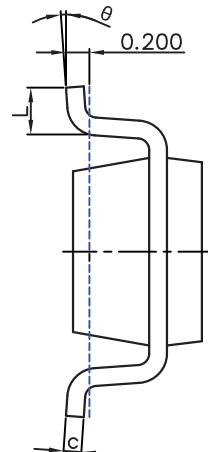
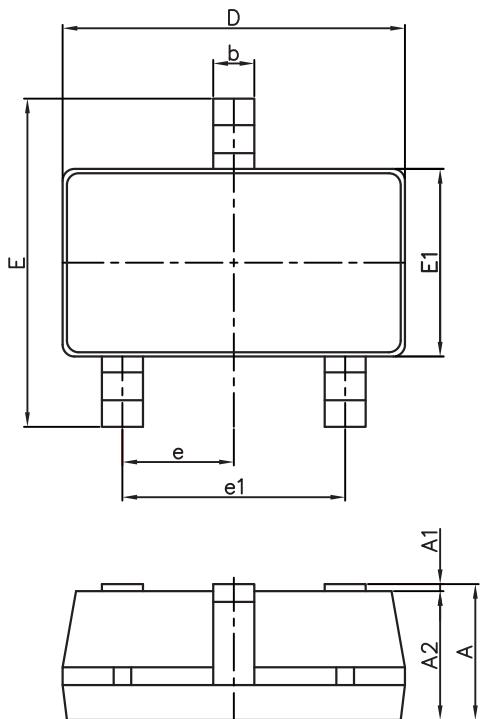
$I_S$  —  $V_{SD}$





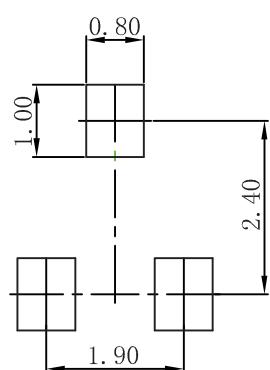
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### SOT23-3L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
K	0°	8°	0°	8°

### SOT23-3L Suggested Pad Lay out



Note:  
1. Controlling dimension: in millimeters.  
2. General tolerance:  $\pm 0.05\text{mm}$ .  
3. The pad layout is for reference purposes only.